commodore
semiconductor group
MOS TECHNOLOGY, INC.
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2316 STATIC READ ONLY MEMORY (2048x8)

DESCRIPTION

The 2316 high performance read only memory is organized 2048 words by 8 bits with access times of less than 450 ns. This ROM is designed to be compatible with all microprocessor and similar applications where high performance, large bit storage and simple interfacing are important design considerations.

The 2316 operates totally asynchronously. No clock input is required. The three programmable chip select inputs allow eight 16K ROMS to be OR-tied without external decoding.

Designed to replace two 2708 8K EPROMS, the 2316 can eliminate the need to redesign printed circuit boards for volume mask programmed ROMS after prototyping with EPROMS.

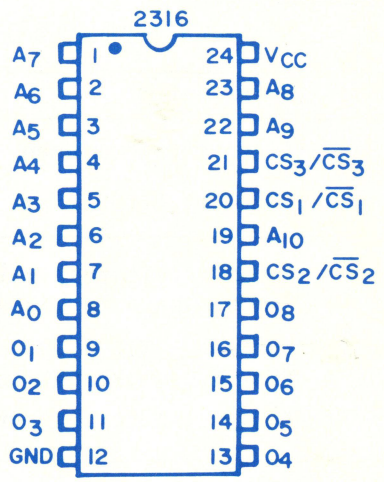
- 400mV Noise Immunity on Inputs
- 2048 x 8 Bit Organization
- Single +5 Volt Supply
- Access Time - 450 ns (max)
- Totally Static Operation
- TTL Compatible
- Three-State Outputs for Wire-OR Expansion
- Three Programmable Chip Selects
- Pin Compatible with 2716 EPROM
- Replacement for two 2708s
- 2708/2716 EPROMS Accepted as Program Data Inputs

ORDERING INFORMATION:

Part Number*	Package Type	Access Time	Temperature Range
MPS2316	Molded	450 ns	0°C to +70°C
MCS2316	Ceramic	450 ns	0°C to +70°C
MPS2316A	Molded	350 ns	0°C to +70°C
MCS2316A	Ceramic	350 ns	0°C to +70°C

*Final Part Number will be assigned by manufacturer.

PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS

Ambient Temperature under Bias	0°C to +70°C
Storage Temperature	-65°C to +150°C
Supply Voltage to Ground Potential	-0.5V to +7.0V
Applied Output Voltage	-0.5V to +7.0V
Applied Input Voltage	-0.5V to +7.0V
Power Dissipation	1.0W

COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

D. C. CHARACTERISTICS

T_A = 0°C to +70°C, V_{CC} = 5.0V ± 5% (unless otherwise specified)

Symbol	Parameter	Min.	Max.	Units	Test Conditions
I_{CC1}	Power Supply Current		100	mA	$V_{IN} = V_{CC}$, V_O = Open, T_A = 0°C
I_{CC2}	Power Supply Current		95	mA	$V_{IN} = V_{CC}$, V_O = Open, T_A = 25°C
I_O	Output Leakage Current		10	µA	Chip Deselected, V_O = 0 to V_{CC}
I_I	Input Load Current		10	µA	V_{CC} = Max. V_{IN} = 0 to V_{CC}
V_{OL}	Output Low Voltage		0.4	Volts	V_{CC} = Min. I_{OL} = 2.1mA
V_{OH}	Output High Voltage	2.4		Volts	V_{CC} = Min. I_{OH} = -400µA
V_{IL}	Input Low Voltage	-0.5	0.8	Volts	See Note 1
V_{IH}	Input High Voltage	2.0	V_{CC}+1	Volts	

A. C. CHARACTERISTICS

T_A = 0°C to +70°C, V_{CC} = 5.0V ± 5% (unless otherwise specified)

Symbol	Parameter	Min.	Max.	Units	Test Conditions
t_{ACC}	Address Access Time		450	ns	See Note 2
t_{CO}	Chip Select Delay		200	ns	
t_{DF}	Chip Deselect Delay		175	ns	
t_{OH}	Previous Data Valid After Address Change Delay	40		ns	

CAPACITANCE

T_A = 25°C, f = 1.0MHz, See Note 3

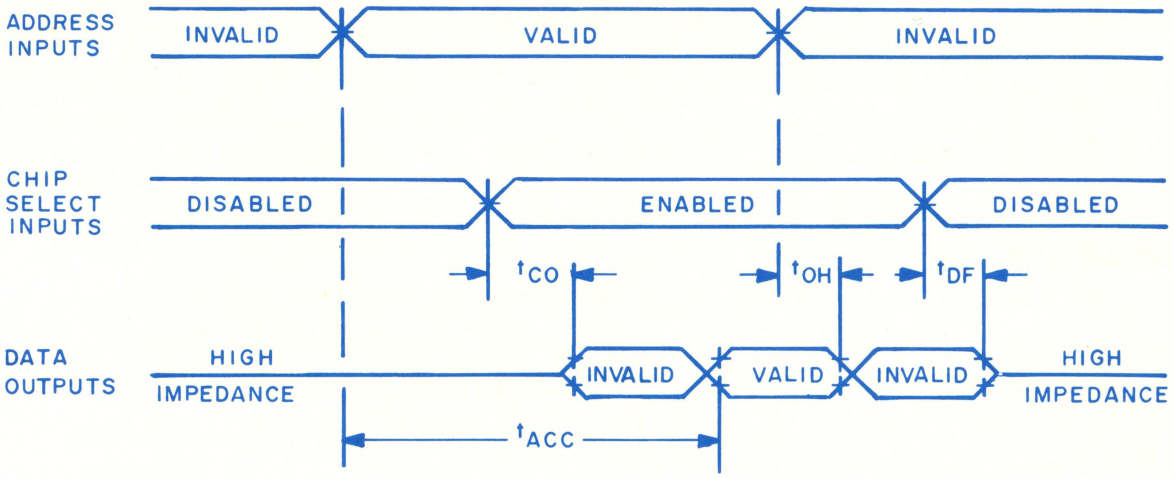
Symbol	Parameter	Min.	Max.	Units	Test Conditions
C_{IN}	Input Capacitance		8	pF	All Pins except Pin under Test Tied to AC Ground
C_{OUT}	Output Capacitance		10	pF	

Note 1: Input levels that swing more negative than -0.5V will be clamped and may cause damage to the device.

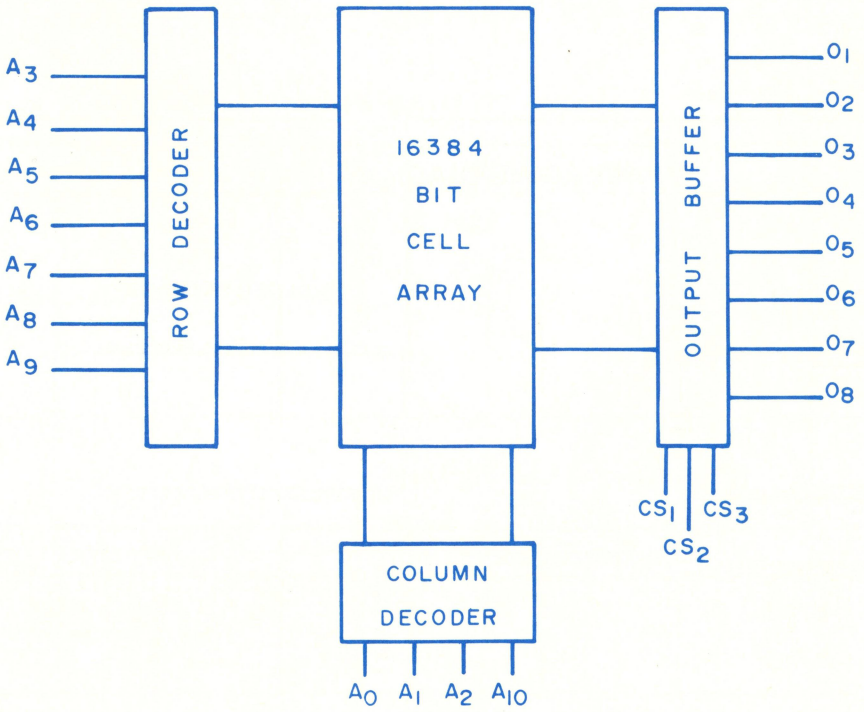
Note 2: Loading 1 TTL + 100 pF, input transition time: 20 ns
Timing measurement levels: input 1.5V, output 0.8V and 2.0V.

Note 3: This parameter is periodically sampled and is not 100% tested.

TIMING DIAGRAM

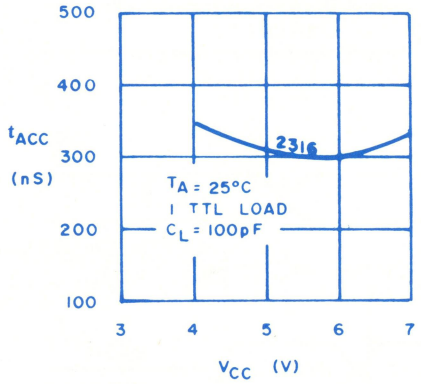


BLOCK DIAGRAM

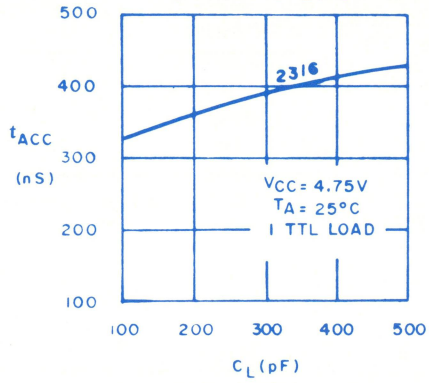


TYPICAL CHARACTERISTICS

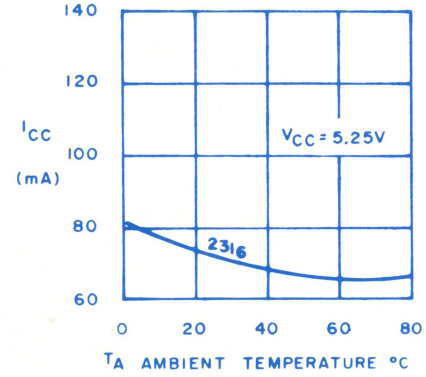
ACCESS TIME VS. SUPPLY VOLTAGE



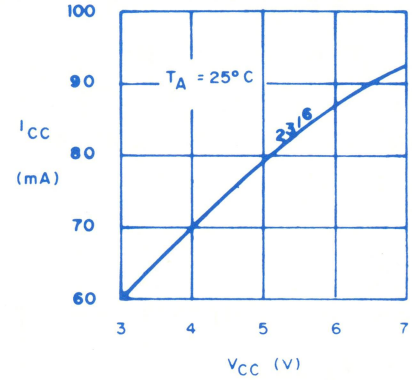
ACCESS TIME VS. CAPACITIVE LOAD



SUPPLY CURRENT VS. AMBIENT TEMPERATURE

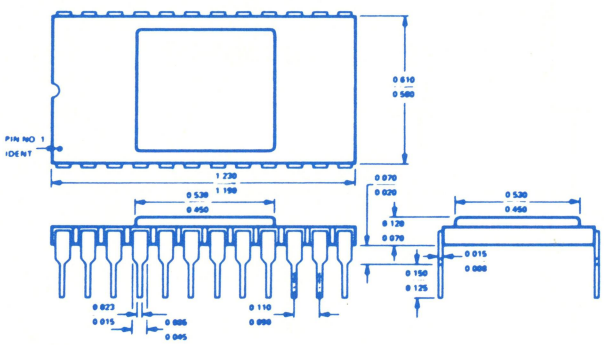


SUPPLY CURRENT VS. SUPPLY VOLTAGE



PACKAGING DIAGRAM

CERAMIC PACKAGE



MOLDED PACKAGE